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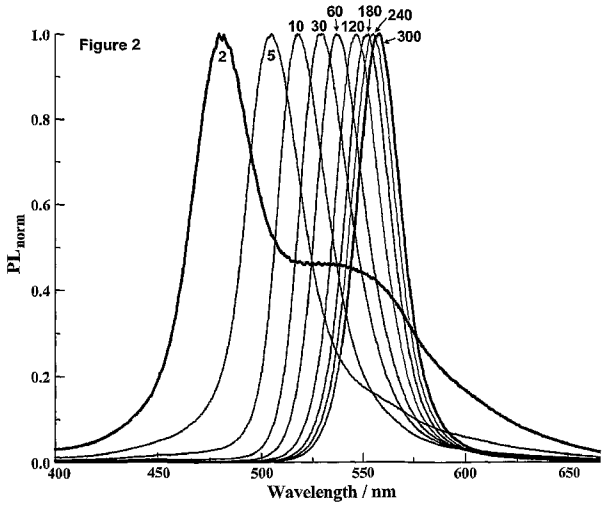
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(54) Title: METHOD OF FORMING A CADMIUM CONTAINING NANOCRYSTAL



(57) Abstract: The present invention provides a method of forming a nanocrystal of the composition CdA, with A being S or Se. The method includes forming in a suitable solvent a solution of cadmium, or a compound thereof, in a form suitable for the generation of a nanocrystal. The solvent includes a compound selected from an ether and an amine. The method further includes bringing the solution to a temperature selected in the range from about 20 °C to about 200 °C. The method also includes adding at the temperature selected in the range from about 20 °C to about 200 °C the element A in a form suitable for the generation of a nanocrystal. Thereby the forming of a nanocrystal of the composition CdA is allowed.

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